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CENTRAL FAX CENTER

MAY 16 2006

Customer No.: 31561  
Application No.: 10/711,939  
Docket No.: 11438-US-PA-0P

AMENDMENT

Amendments to the Specification

Please amend Paragraph 0026 as below:

[Para 26] Referring to FIG. 1 again, a doped region 112 as a portion of the common lower electrode of the storage capacitors formed later is formed in the lower portion of the sidewall of each pillar 110 and in the surface layer of the substrate 100. The portion of the doped region 112 in each pillar 110 serves as a first plate of a capacitor that is described in the Summary of the invention. Meanwhile, the portion of the doped region 112 in the substrate 100 between the pillars [100] 110 is the doped surface layer of the substrate between the pillars that is described in the Summary.